

ABSTRACT

The invention relates to an optical sensor element (10) which comprises, in a semiconductor substrate (1), a light-sensitive region (18) in which charge carriers can be released by irradiation, and two doped regions (15, 16) for receiving the charge carriers released in the light-sensitive region (18). The invention is characterized in that electrodes (13, 14) for generating a field gradient in the light-sensitive region (18) are insulated from the light-sensitive region (18) and are disposed in trenches formed in the surface of the substrate (1).